



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDTA)
- Built-In Biasing Resistor, R2 Only

Part Number	R2 (NOM)	Marking
NK-DDTC114GE	10k Ω	N26
NK-DDTC124GE	22k Ω	N27
NK-DDTC144GE	47k Ω	N28
NK-DDTC115GE	100k Ω	N29

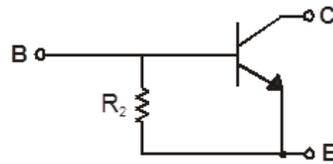
Mechanical Data

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish. Solderable per MIL-STD-202, Method 208③
- Weight: 0.002 grams (Approximate)

SOT523



Top View



Schematic Diagram

Absolute Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	I_C (Max)	100	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

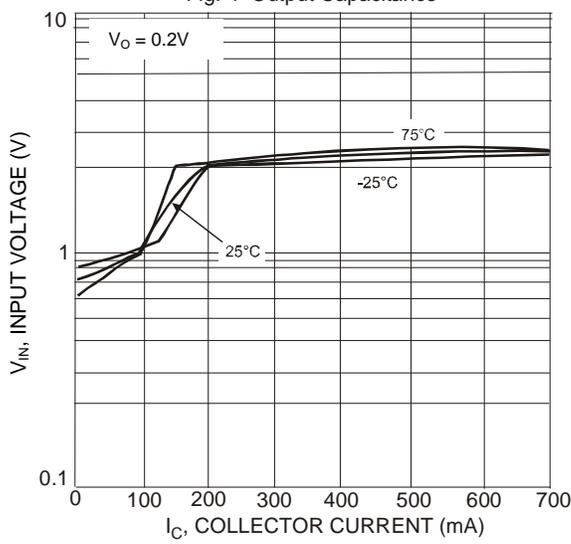
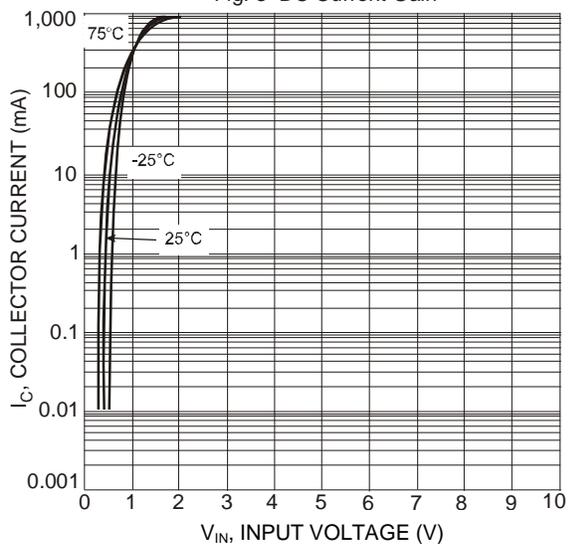
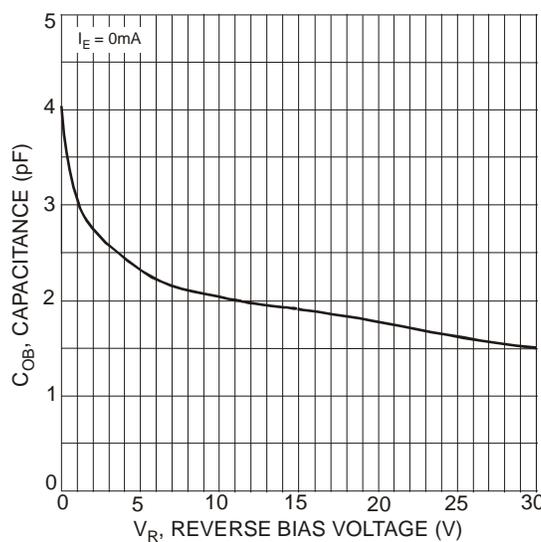
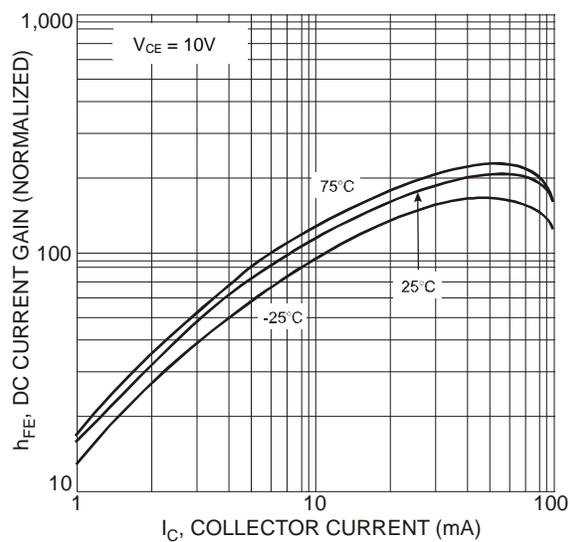
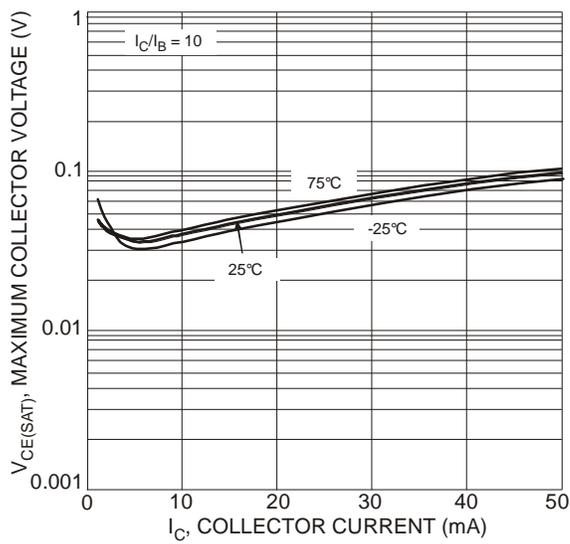
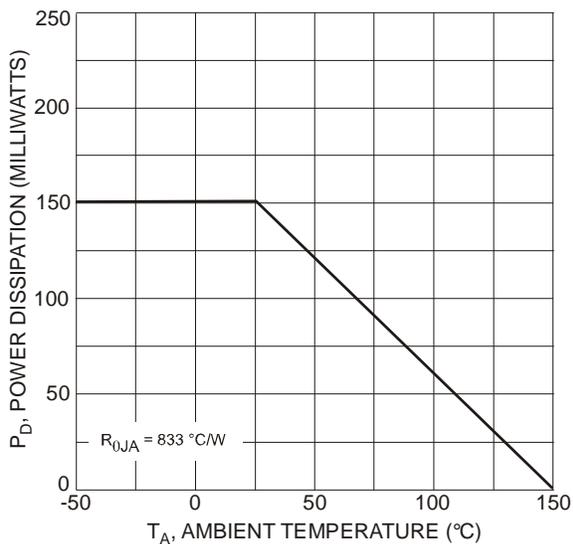
Characteristic	Symbol	Value	Unit
Power Dissipation	P_D	150	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{\theta JA}$	833	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	50	—	—	V	$I_C = 50\mu\text{A}$
Collector-Emitter Breakdown Voltage	BV_{CEO}	50	—	—	V	$I_C = 1\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	5	—	—	V	$I_E = 720\mu\text{A}$, NK-DDTC114GE $I_E = 330\mu\text{A}$, NK-DDTC124GE $I_E = 160\mu\text{A}$, NK-DDTC144GE $I_E = 72\mu\text{A}$, NK-DDTC115GE
Collector Cutoff Current	I_{CBO}	—	—	0.5	μA	$V_{CB} = 50\text{V}$
Emitter Cutoff Current	I_{EBO}	300 140 65 30	—	580 260 130 58	μA	$V_{EB} = 4\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	—	0.3	V	$I_C = 10\text{mA}$, $I_B = 0.5\text{mA}$
DC Current Transfer Ratio	h_{FE}	30 56 68 82	—	—	—	$I_C = 5\text{mA}$, $V_{CE} = 5\text{V}$
Bleeder Resistor (R_2) Tolerance	ΔR_2	-30	—	+30	%	—
Gain-Bandwidth Product (Note 6)	f_T	—	250	—	MHz	$V_{CE} = 10\text{V}$, $I_E = -5\text{mA}$, $f = 100\text{MHz}$

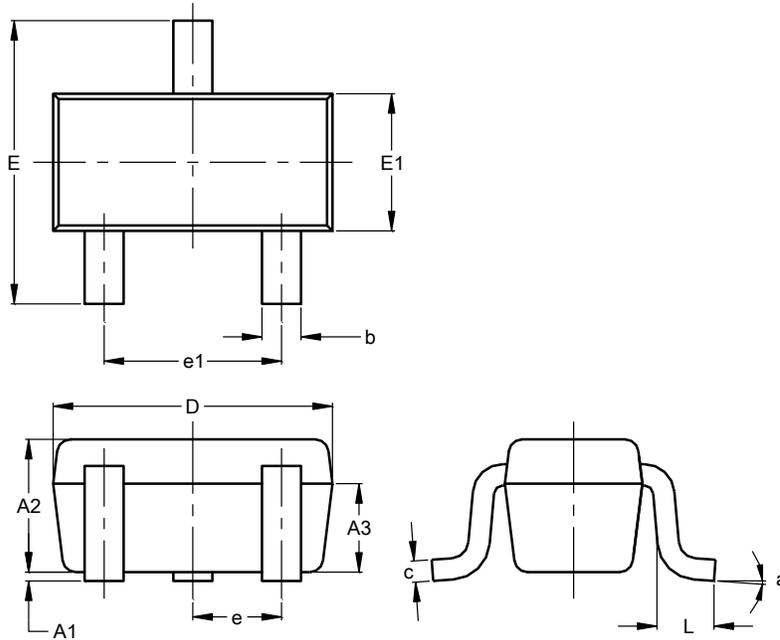
Notes: 5. Mounted on FR-4 PC Board with minimum recommended pad layout.
6. Transistor only.

Typical Curves – NK-DDTC114GE



Package Outline Dimensions

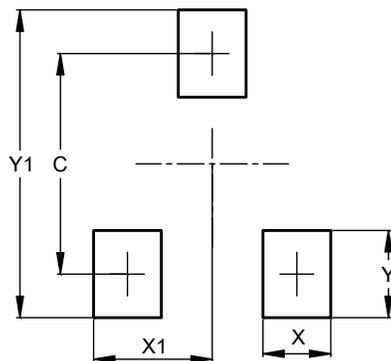
SOT523



SOT523			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.60	0.80	0.75
A3	0.45	0.65	0.50
b	0.15	0.30	0.22
c	0.10	0.20	0.12
D	1.50	1.70	1.60
E	1.45	1.75	1.60
E1	0.75	0.85	0.80
e	0.50 BSC		
e1	0.90	1.10	1.00
L	0.20	0.40	0.33
a	0°	--	8°
All Dimensions in mm			

Suggested Pad Layout

SOT523



Dimensions	Value (in mm)
C	1.29
X	0.40
X1	0.70
Y	0.51
Y1	1.80